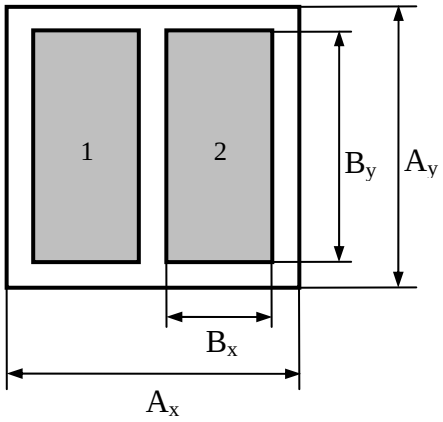
VSP-MIKRON

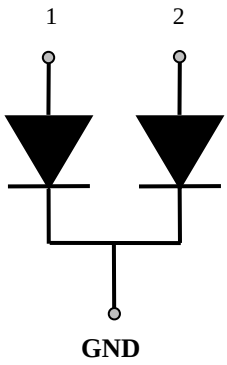
RoHS

Rev.1. March 2010.

LCD-150N1

Dual chip low capacitance diode on N+ type substrate.





Mechanical date: A_x= 650um, A_y=600um.
B_x=235um, B_y=495um

Schematic and pinning diagram.

Chip thickness: 230+/-20um
Scribe Line width - 60um.
Top Metal: Al - for wire bonding.
Back side - Cathode: Ti-Ni-Ag for soldering.

Limiting values

Parameter	Symbol	Conditions	Value	Unit
Reverse Stand-off voltage	V_{RWM}	-	5	V
Peak Pulse Power	P_{pp}	t_p=8/20us	25*	W
Peak Pulse Current	I_{pp}	t_p=8/20us	16,0*	A
Electrostatic Discharge	V_{ESD}	IEC 61000-4-2, level 4.	>8 (Contact); >15 (Air).	kV
Max.junction temperature	T_j	-	+150	ºC

Characteristics (Tj=25ºC)

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{BR}	Breakdown voltage	I_R=1mA	50,0	-	-	V
I_R	Reverse leakage current	V_R=50,0V	-	-	0,9	uA
V_F	Peak forward voltage	I_F=5A, t_p= 8/20uS I_F=16,0A, t_p=8/20uS	-	-	2,0* 4,0*	V
C_J	Diode capacitance	V_R=0 V, f =1MHz	-	-	5,0	pF

*- For Device testing